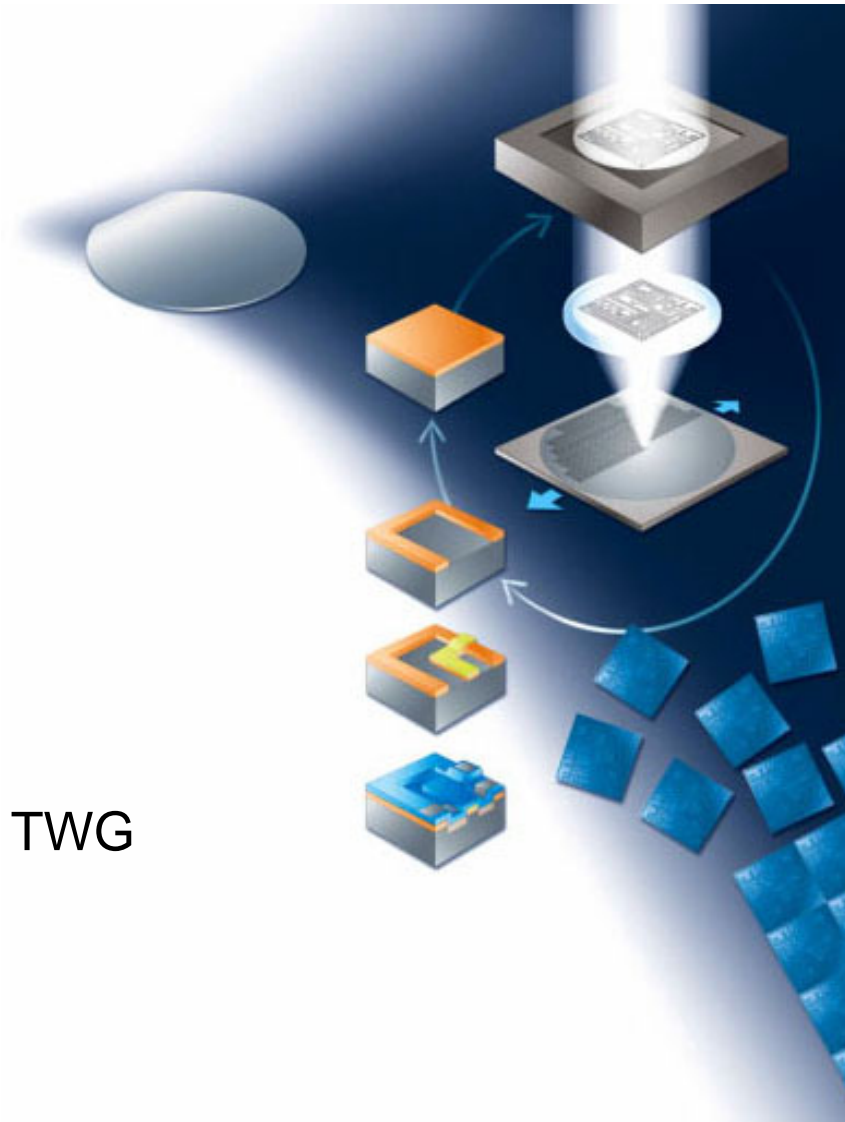


Lithography Optics Division

**EUVL**  
**Optics lifetime and**  
**contamination**  
**European update**

IEUVI Optics Contamination/Lifetime TWG  
Thomas Stein

19.10.2006





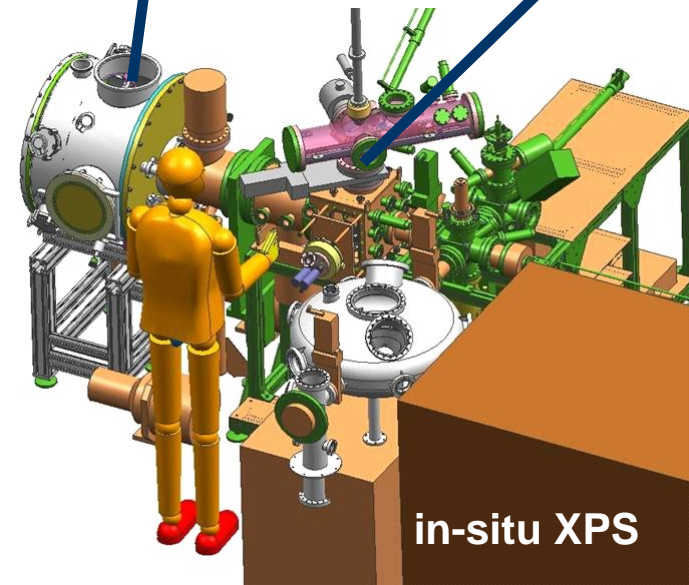
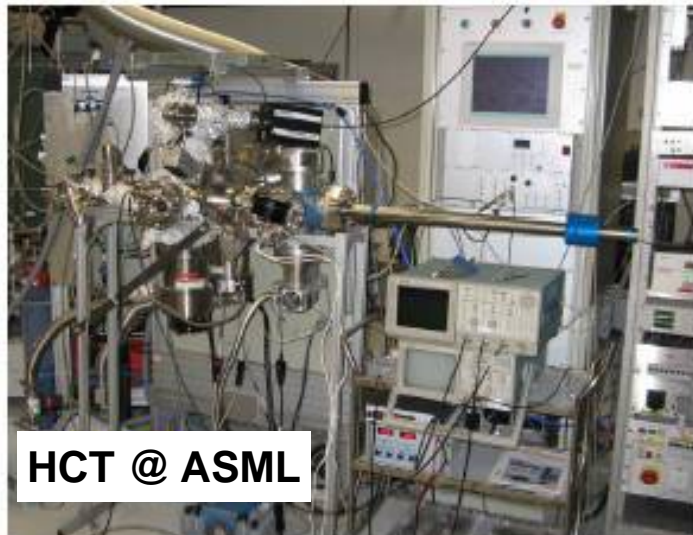
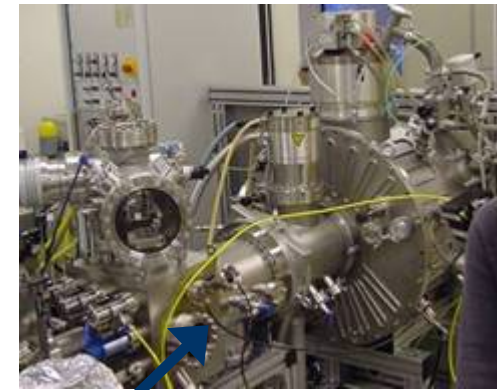
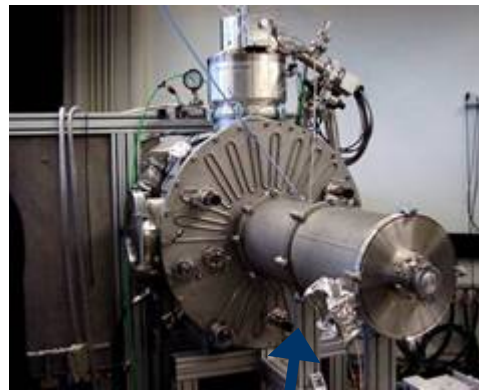
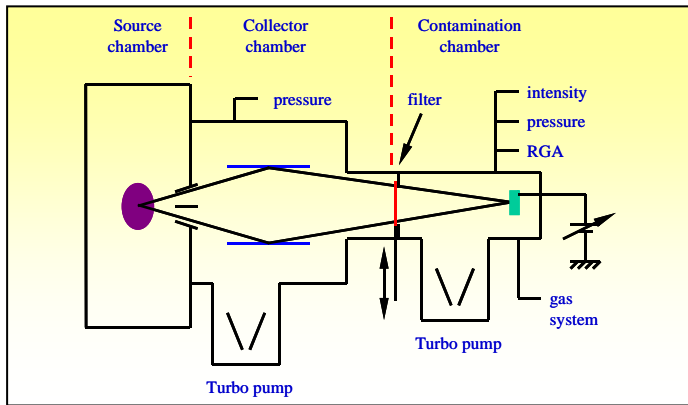
## Overview

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- General and strategy
- Recent results
- Outlook HVM

# Pulsed beamlines for optics contamination investigation

\*HCT = hollow-cathode-triggered discharge source

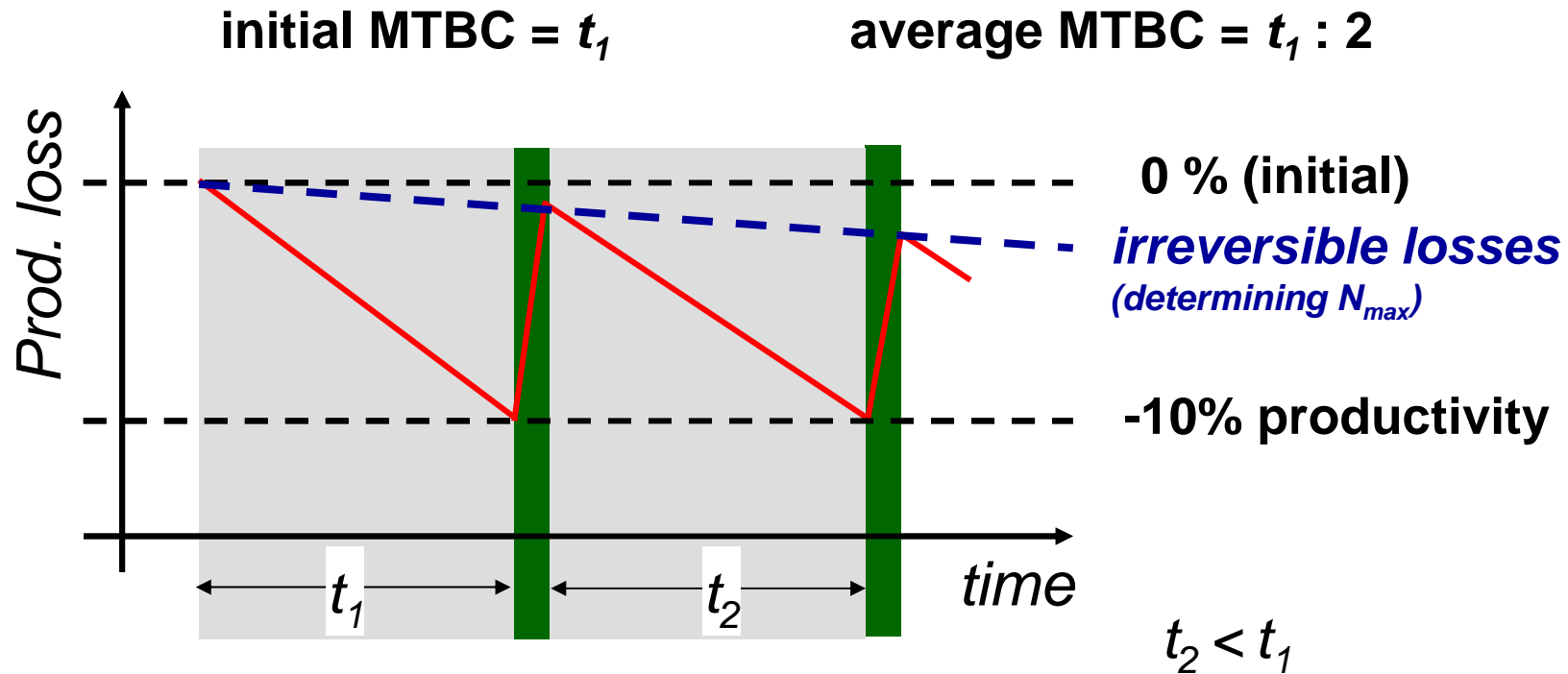


EBL @ TNO

Source collector geometry and cleaning similar to ADT

## General optics usage strategy

- Clean, grease-free vacuum system
- Repetitive exposure and cleaning
- time between cleaning decreases over time (non-cleanable losses)



**LT = MTBC \*  $N_{max}$**

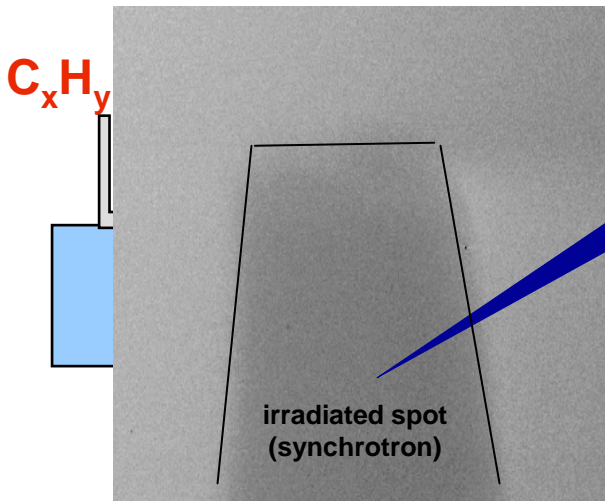
$N_{max}$ : maximum number of possible cleaning cycles

MTBC = mean time between cleanings

# Contamination mitigation is required to maintain tool productivity

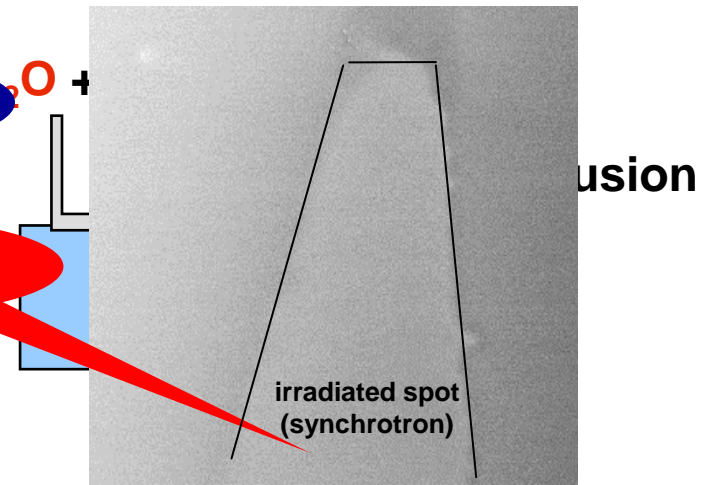
## Carbon growth:

1% loss per nm carbon



## Oxidation:

3% loss per nm additional oxide



Reversible  
Irreversible

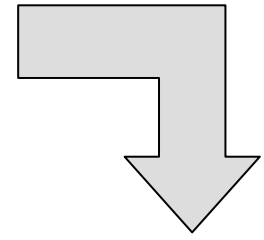
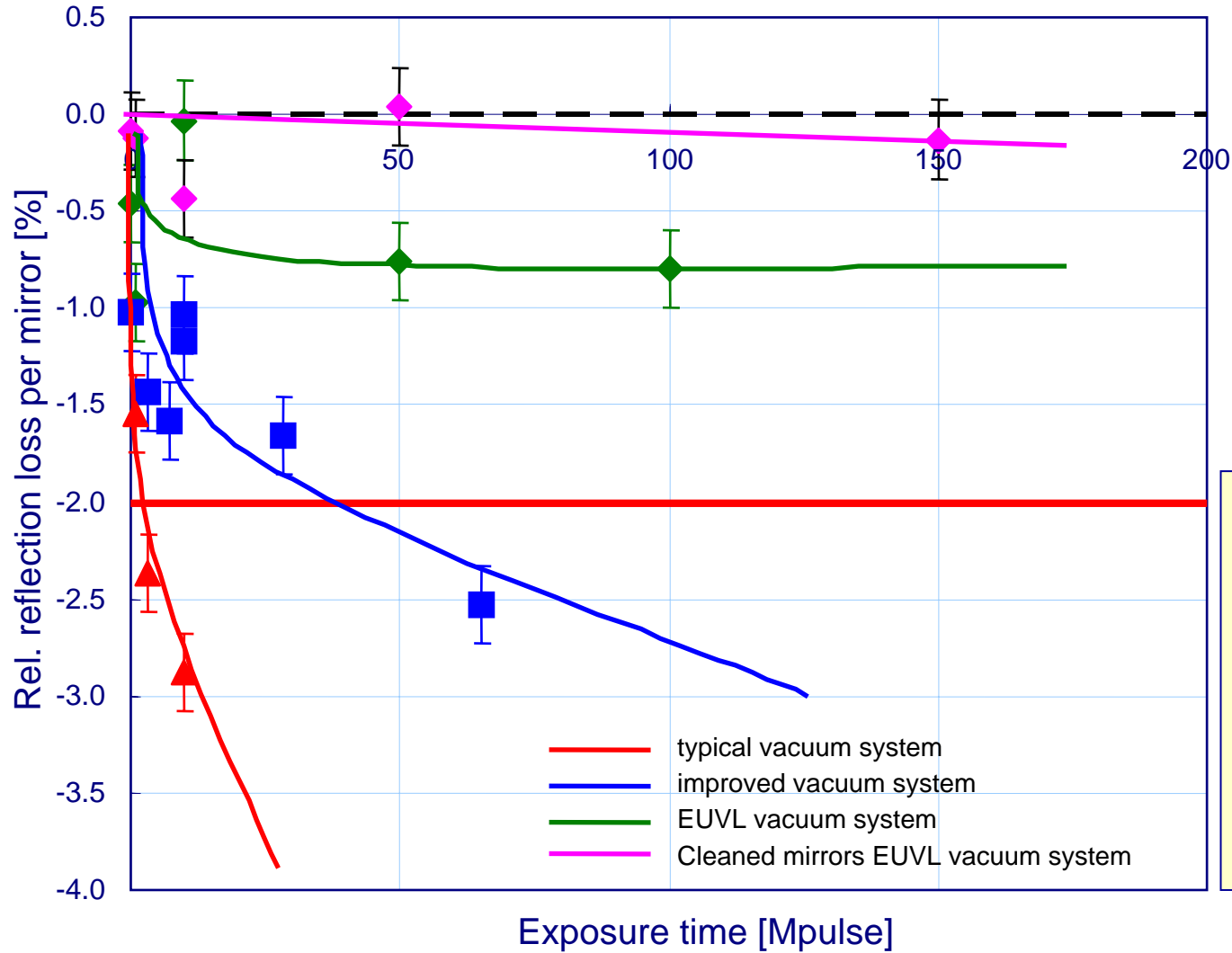
### Optics contamination mitigation strategy includes

- clean vacuum environment (materials, gases, equipment...)
- selection of materials applied in vacuum
- oxidation resistant mirror coatings
- carbon cleaning, without mirror degradation

intensity and pressure dependence of mirror degradation ?  
→ next slides

**Note: reflectivity loss does impact tool productivity rather than imaging performance**

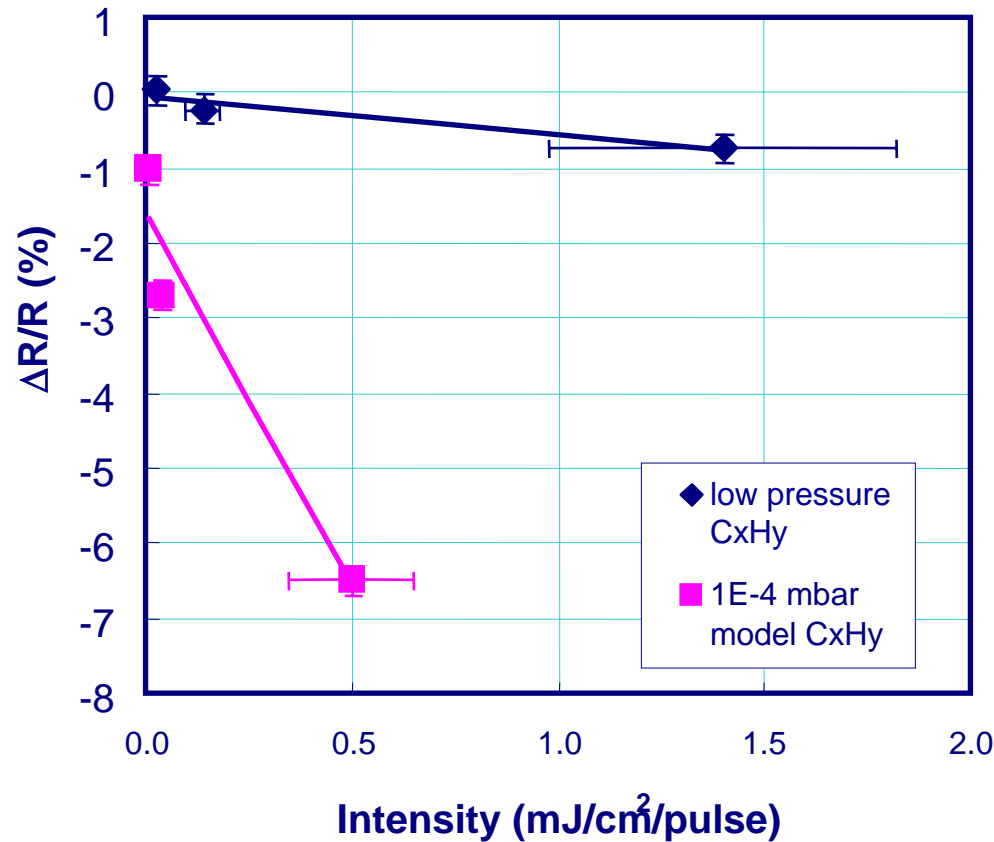
# Overview carbon growth behaviour under different conditions



**Given experimental data, we expect mild carbon growth for clean lithotool vacuum environment.**

T Stain I E I M I Ontire Contamination/ I f i t i m e T M / Q B a r a l i n n a 1 0 1 0 2 0 0 6

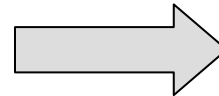
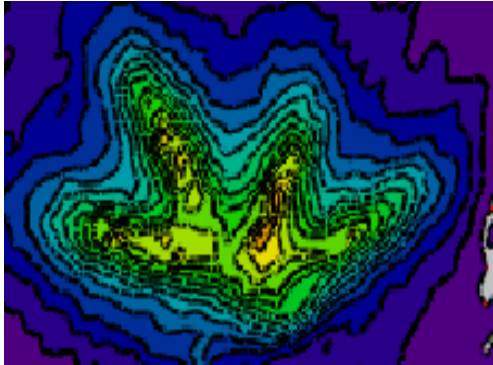
## Linear dependence of intensity vs. carbon growth



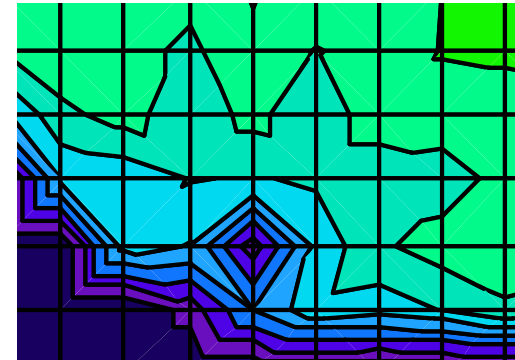
- Intensity is a scaling parameter → linear dependence for contamination rate with respect to intensity
- intensity and pressure dependence of carbon growth has been shown

# Amount of C-growth on mirrors depends on EUV intensity

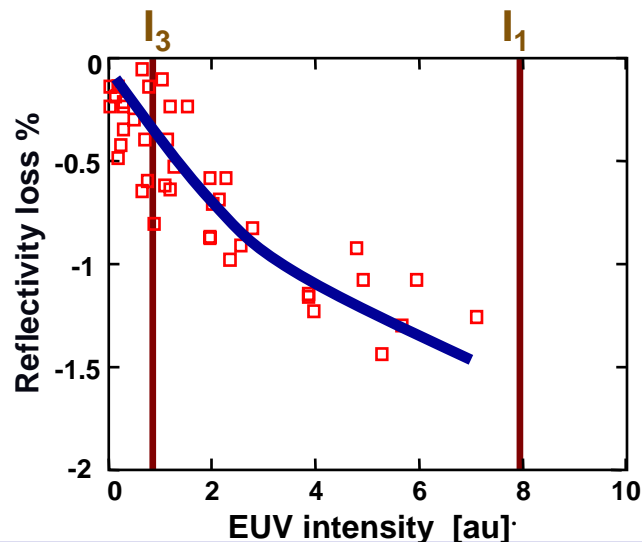
Illumination profile



reflectivity map



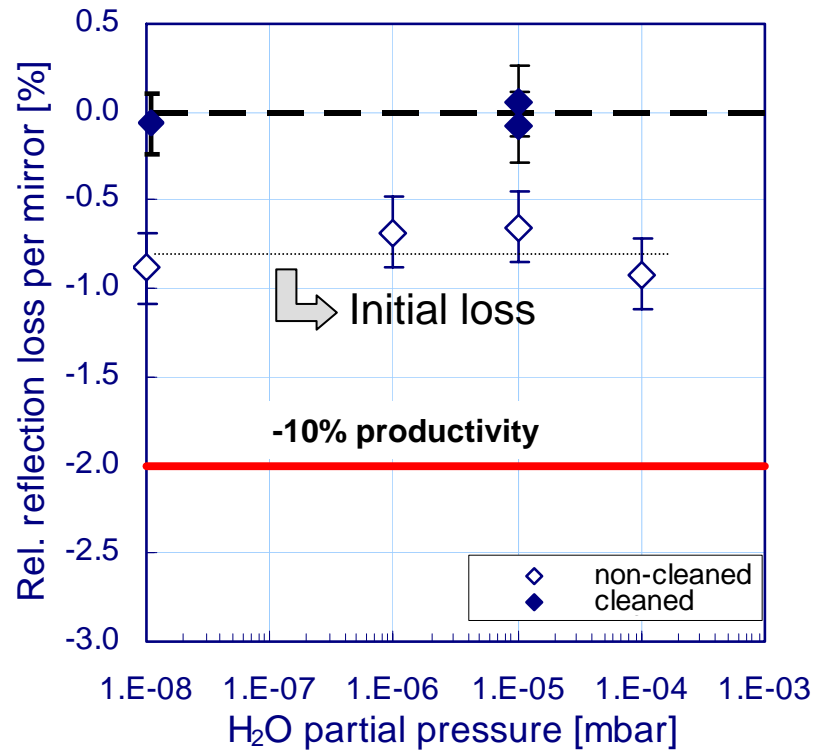
## Local reflectivity loss vs EUV power



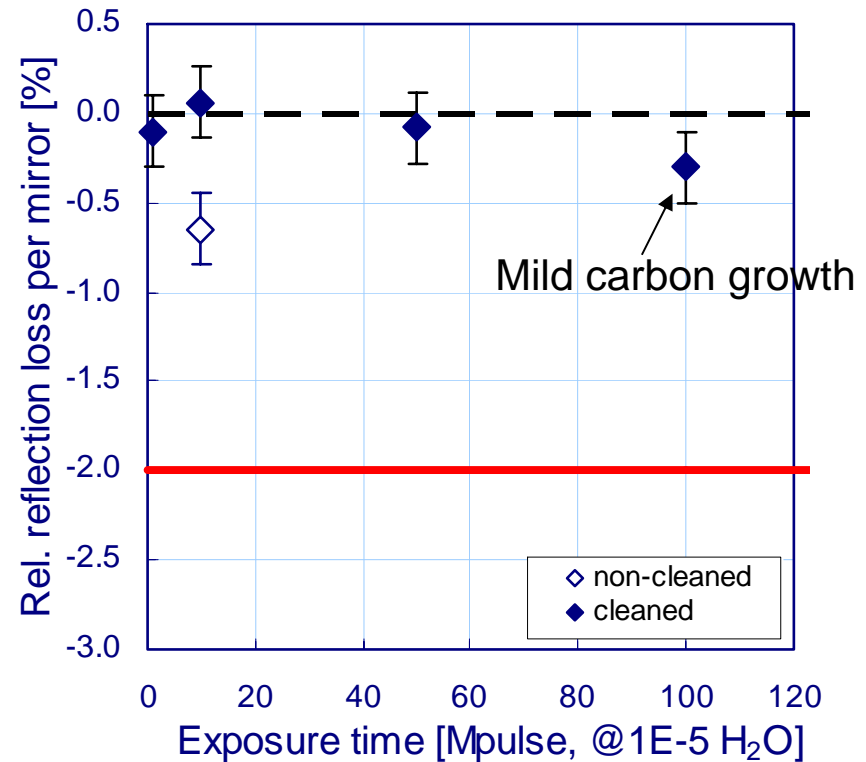
- the first mirrors in the illuminator see the highest EUV intensity and thus the highest carbon growth rate
- Intensity at the POB mirrors is substantially lower

# Optics reflectivity is dominantly influenced by carbon growth

**Influence of H<sub>2</sub>O**



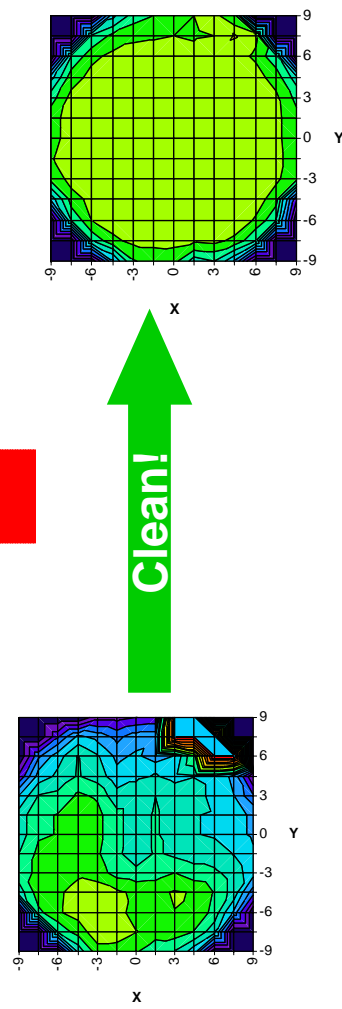
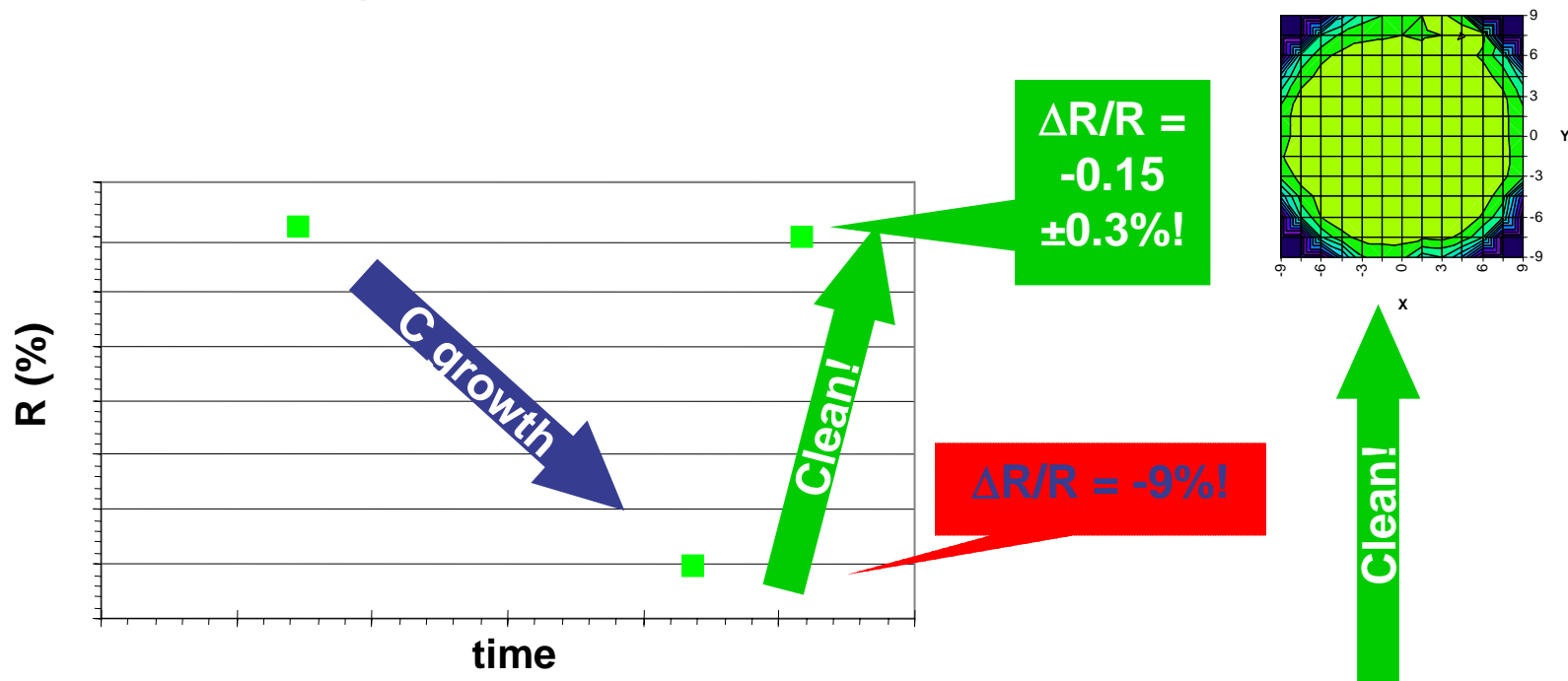
**Influence of C-growth**



- Oxidation due to water pressures upto 1E-05 mbar not observed
- Carbon growth is dominantly contributing to productivity with time

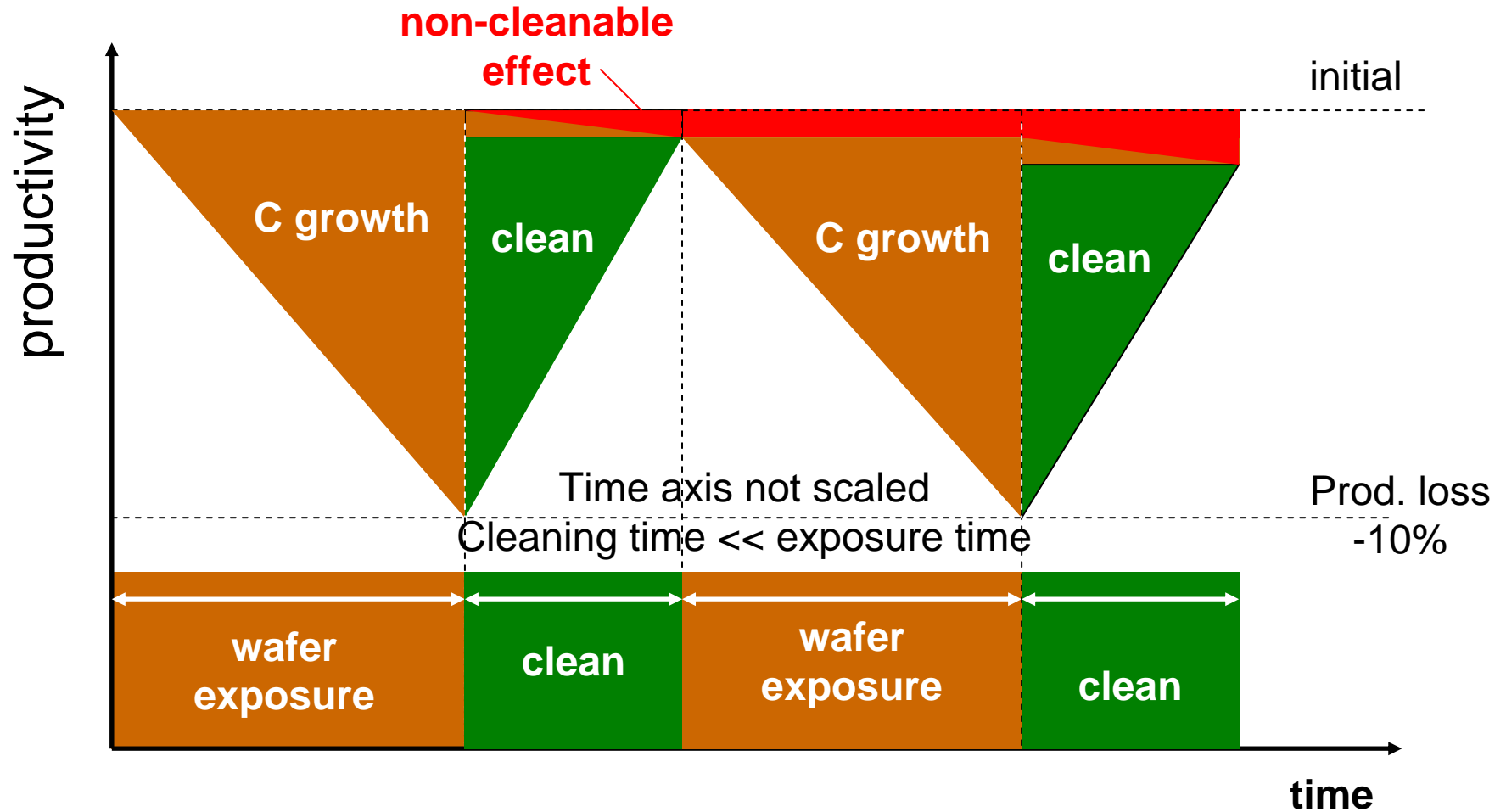
# C-growth is removable with cleaning

## Cleaning result



**Cleaning on heavily carbonised mirrors up to initial reflectance has been experimentally proven!!!**

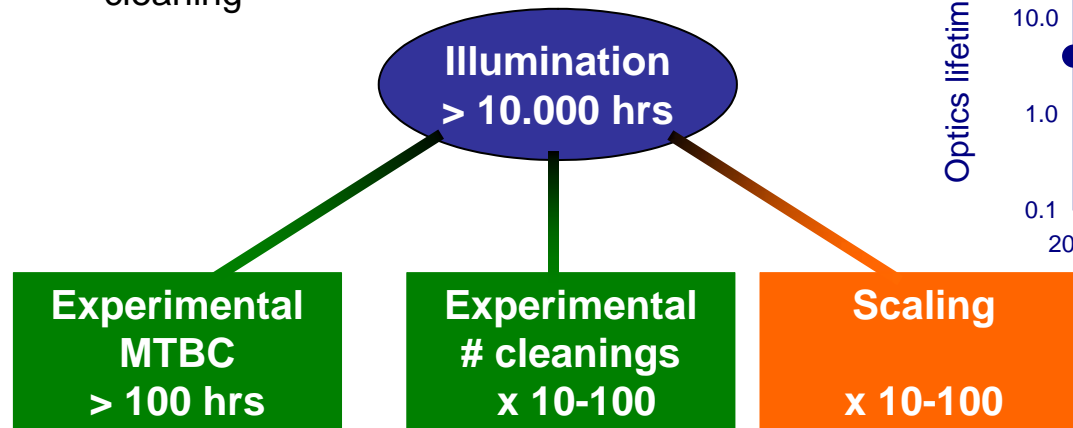
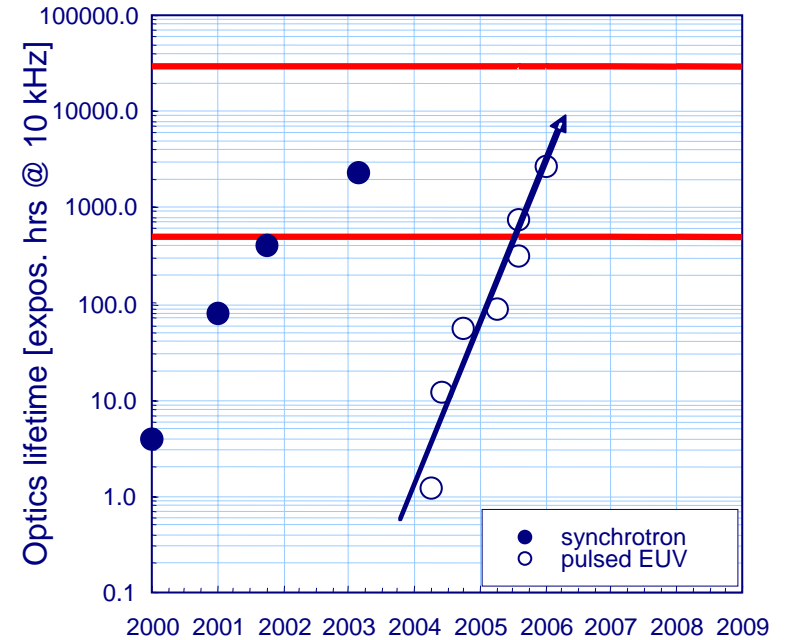
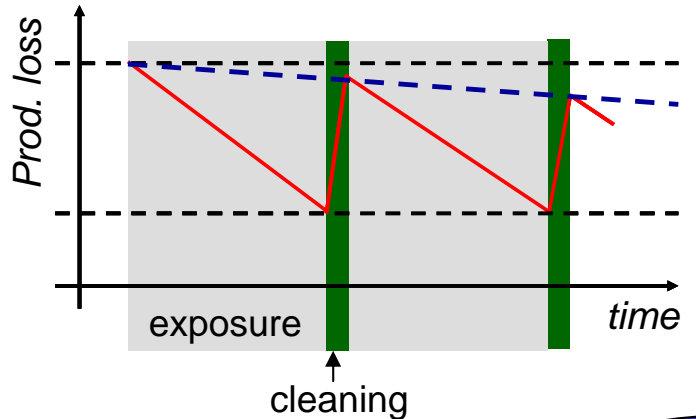
# Lifetime/contamination mitigation strategy (ADT)



T. Stein, IEUVI Optics Contamination/Lifetime TWG, Barcelona, 19.10.2006

Depending on environmental conditions and source power several thousand wafers can be exposed between cleaning actions

## Working focus for HVM optics contamination work



Improvement in all relevant fields needed for HVM lifetime requirements.

**We are not there yet, but we are on track for HVM optics lifetime ....**

## Acknowledgements

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**Carl Zeiss SMT AG, Oberkochen, Germany**



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**PTB, Berlin, Germany**



**Philips, Eindhoven, The Netherlands**



**ALS, Berkeley, USA**